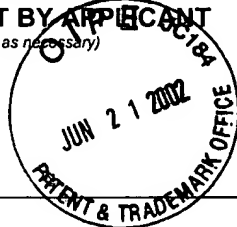


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Application Number	09/943134
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Unknown

Sheet 1 of 3

Attorney Docket No: 01303.020US1

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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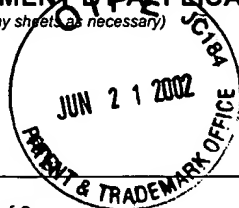
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Sheet 2 of 3

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Application Number	09/943134
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	22818
Examiner Name	Unknown

Attorney Docket No: 01303.020US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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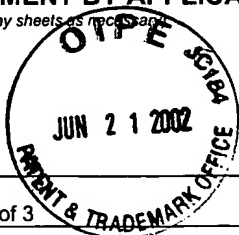
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Application Number	09/943134
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First Named Inventor	Forbes, Leonard
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Examiner Name	Unknown

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